

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Surface-mounted package
- ☒ Super Trench
- ☒ Advanced trench cell design
- ☒ MSL1

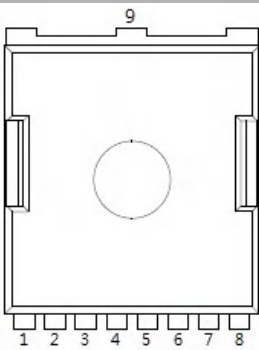
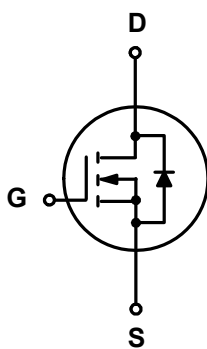
1.2 Applications

- ☒ BMS
- ☒ Drones
- ☒ High power inverter system
- ☒ Light electric vehicles

1.3 Quick reference

- ☒ $BV \geq 100 \text{ V}$
- ☒ $P_{tot} \leq 300 \text{ W}$
- ☒ $I_D \leq 250 \text{ A}$
- ☒ $R_{DS(ON)} \leq 1.6\text{m}\Omega @ V_{GS} = 10 \text{ V}$
- ☒ $R_{DS(ON)} \leq 2.5\text{m}\Omega @ V_{GS} = 6 \text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)	 Top View TOLL	
2,3,4,5,6,7,8	Source(S)		
9	Drain(D)		

3. Limiting Values

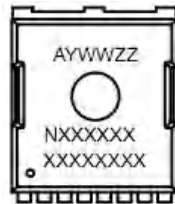
Symbol	Parameter		Rating	Unit
V_{DS}	Drain-Source Voltage		100	V
V_{GS}	Gate-Source Voltage		± 20	V
I_D Note3	Drain Current	$T_C = 25\text{ }^{\circ}\text{C}$	250	A
		$T_C = 100\text{ }^{\circ}\text{C}$	206	A
I_{DM} Note2	Pulsed Source Current	$T_C = 25\text{ }^{\circ}\text{C}$	1000	A
I_S	Diode Forward Current	$T_C = 25\text{ }^{\circ}\text{C}$	250	A
E_{AS}	Single Pulsed Avalanche Energy	$L = 1.0\text{mH}$	2265	A
P_{tot}	Total Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	300	W
$R_{\theta JA}$ Note1	Thermal Resistance- Junction to Ambient		49	$^{\circ}\text{C} / \text{W}$
$R_{\theta JC}$	Thermal Resistance- Junction to Case		0.5	$^{\circ}\text{C} / \text{W}$
T_{stg}	Storage Temperature		-55~175	$^{\circ}\text{C}$
T_J	Junction Temperature		175	$^{\circ}\text{C}$

Note 1 : Surface Mounted on 1 in² pad area, $t \leq 10$ sec.

Note 2 : Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Note 3 : Limited by bonding wire.

4. Marking Information

Product Name	Marking
UP016N10T	

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
UP016N10T	TOLL-8L			2000	

6. Electrical Characteristics ($T_A=25^\circ$ Unless Otherwise Noted)

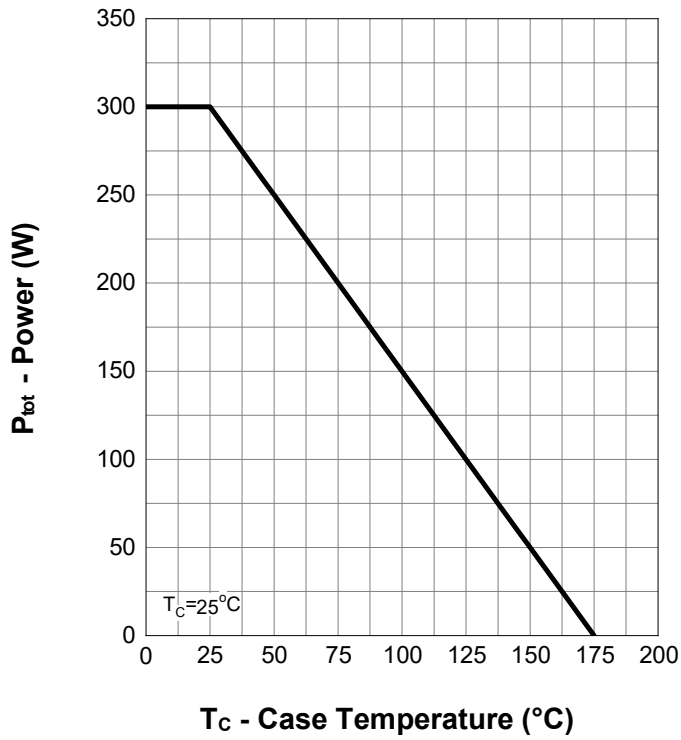
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _{DS} = 250 μA	100	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _{DS} = -250 μA	2	-	4	V
I _{DSS}	Drain Leakage Current	V _{DS} = 80 V, V _{GS} = 0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	±100	nA
R _{DS(ON)} ^{Note1}	On-State Resistance	V _{GS} = 10 V, I _{DS} = 50 A	-	1.3	1.6	mΩ
		V _{GS} = 6 V, I _{DS} = 30 A	-	1.9	2.5	
Diode Characteristics						
V _{SD} ^{Note1}	Diode Forward Voltage	I _{SD} =50 A, V _{GS} = 0 V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _{DS} = 50 A, V _{GS} = 0 V dI _{SD} /dt = 100 A/μs	-	83	-	nS
Q _{rr}	Reverse Recovery Charge		-	142	-	nC
Dynamic Characteristics ^{Note2}						
C _{iss}	Input Capacitance	V _{GS} = 0 V, V _{DS} = 50 V Frequency = 1 MHz	-	9936	-	pF
C _{oss}	Output Capacitance		-	1708	-	
C _{rss}	Reverse Transfer Capacitance		-	67	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} = 50 V, V _{GEN} = 10 V, R _G = 3.9 Ω, R _L = 1 Ω, I _{DS} = 50 A	-	31	-	nS
t _r	Turn-on Rise Time		-	101	-	
t _{d(off)}	Turn-off Delay Time		-	121	-	
t _f	Turn-off Fall Time		-	102	-	
Gate Charge Characteristics ^{Note2}						
Q _g	Total Gate Charge	V _{DS} = 50 V, V _{GS} = 10 V, I _{DS} = 50 A	-	190	-	nC
Q _{gs}	Gate-Source Charge		-	51	-	
Q _{gd}	Gate-Drain Charge		-	56	-	

Note 1: Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

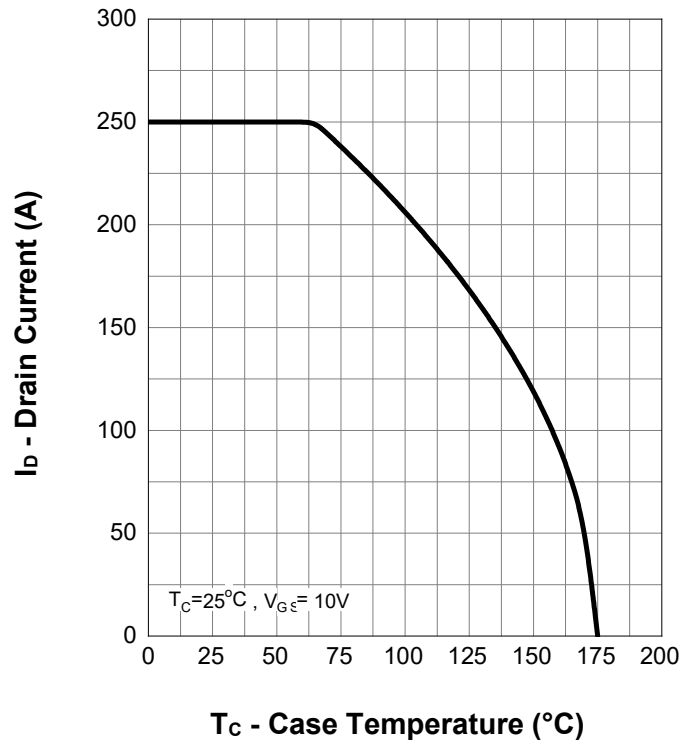
Note 2: Guaranteed by design, not subject to production testing.

7. Typical Characteristics

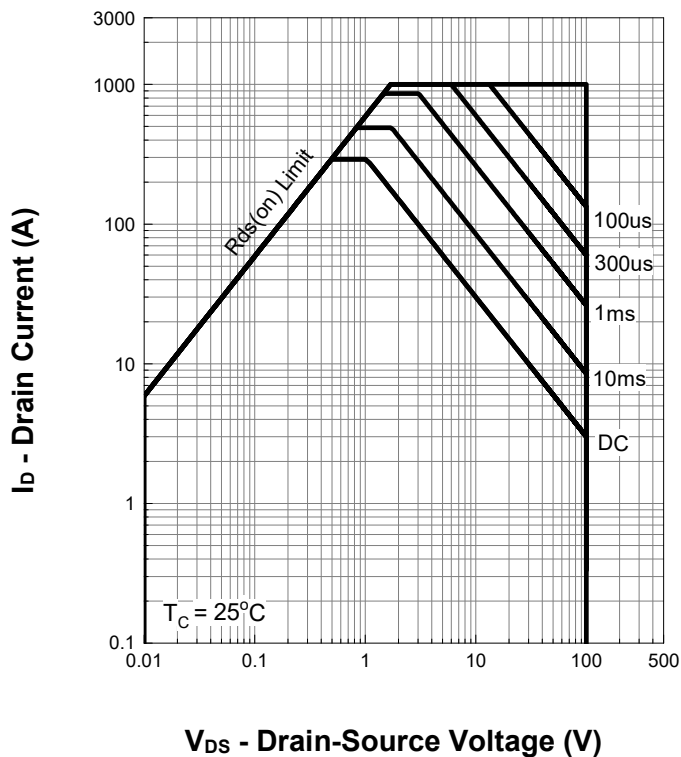
Power Capability



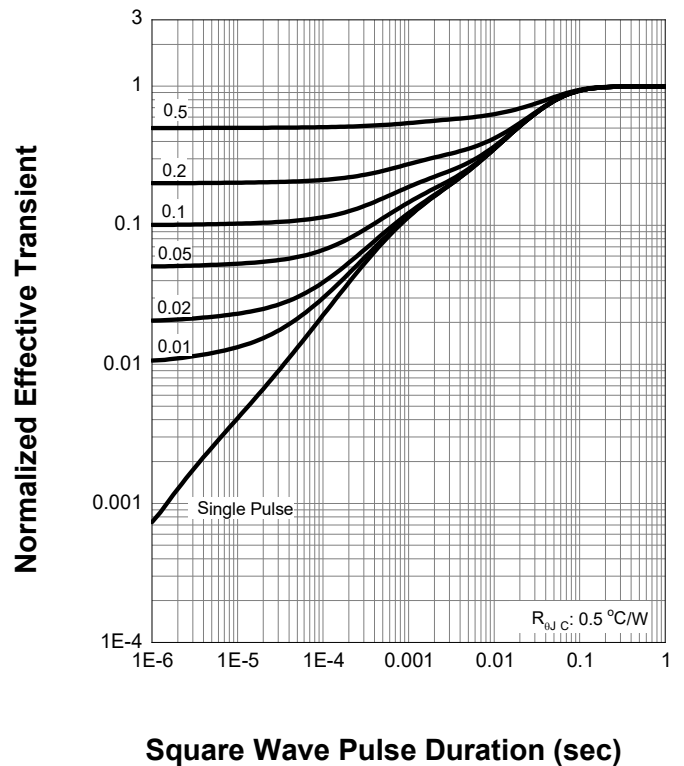
Current Capability



Safe Operating Area

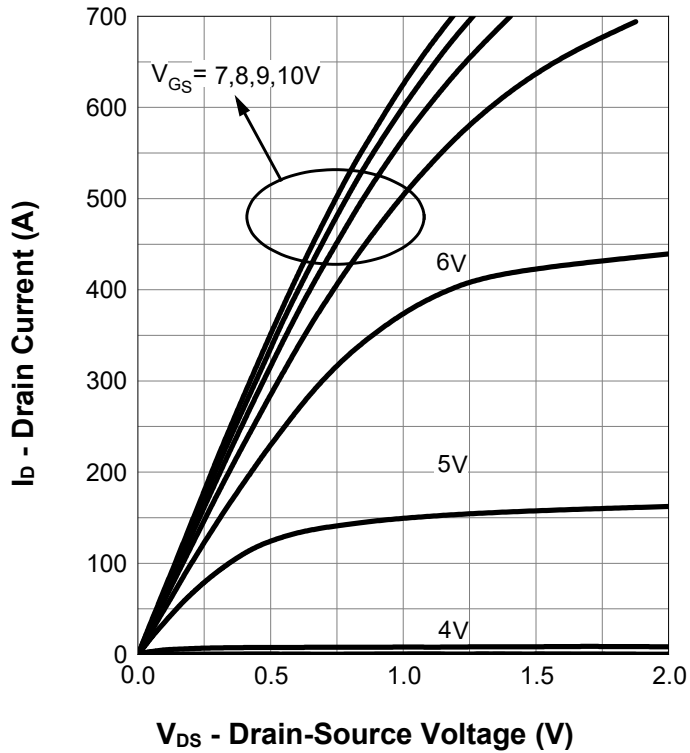


Transient Thermal Impedance

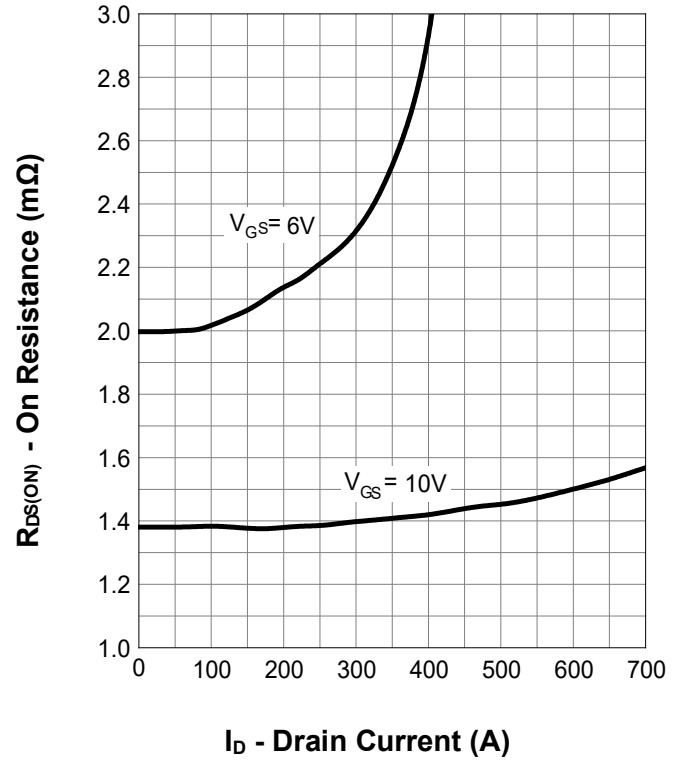


7. Typical Characteristics (cont.)

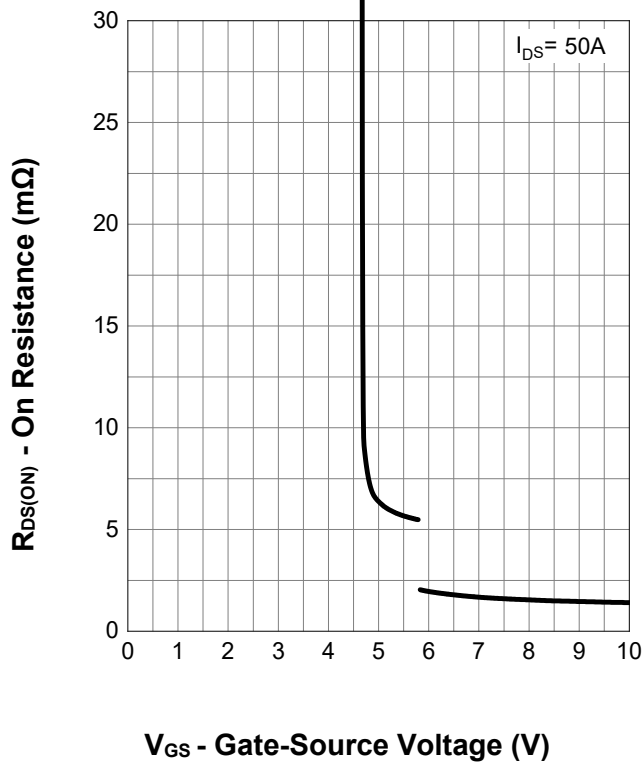
Output Characteristics



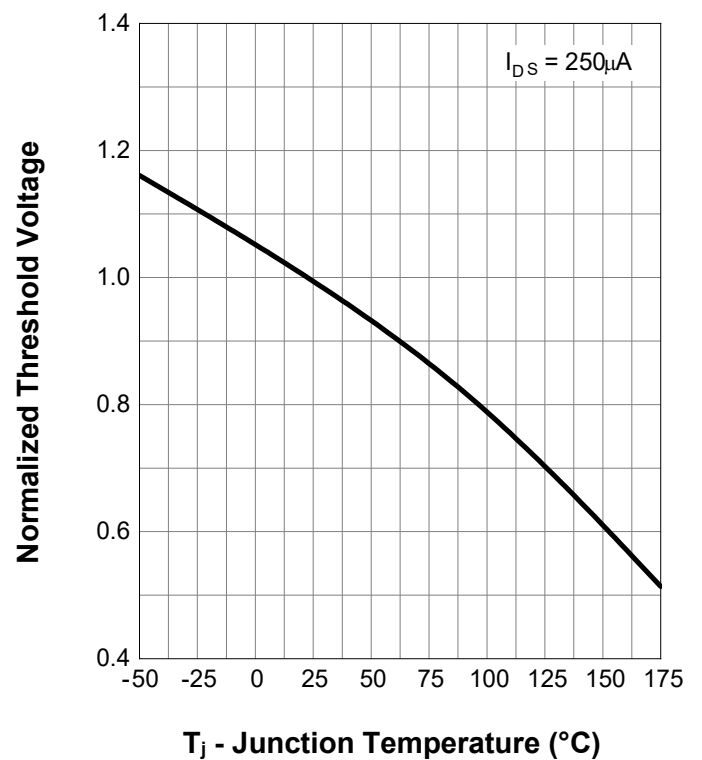
On Resistance



Transfer Characteristics

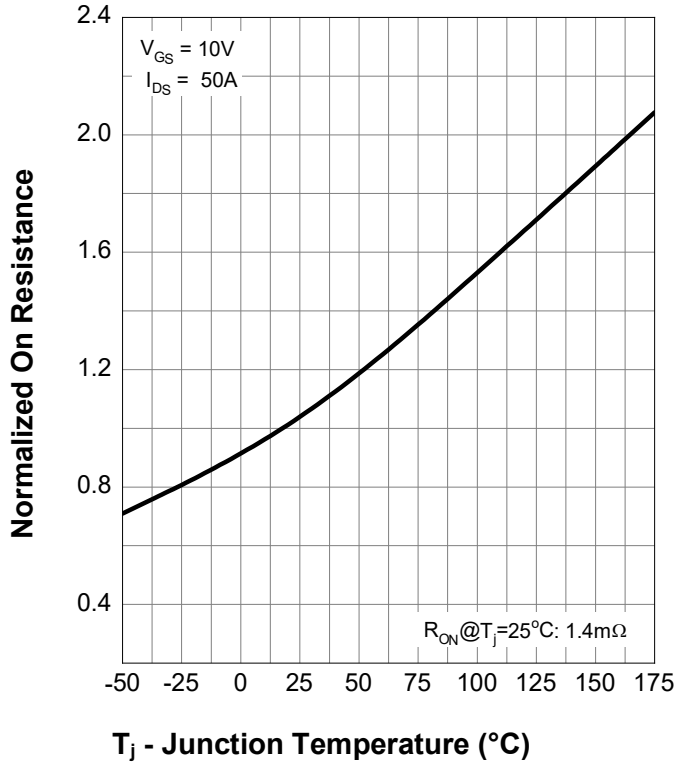


Normalized Threshold Voltage

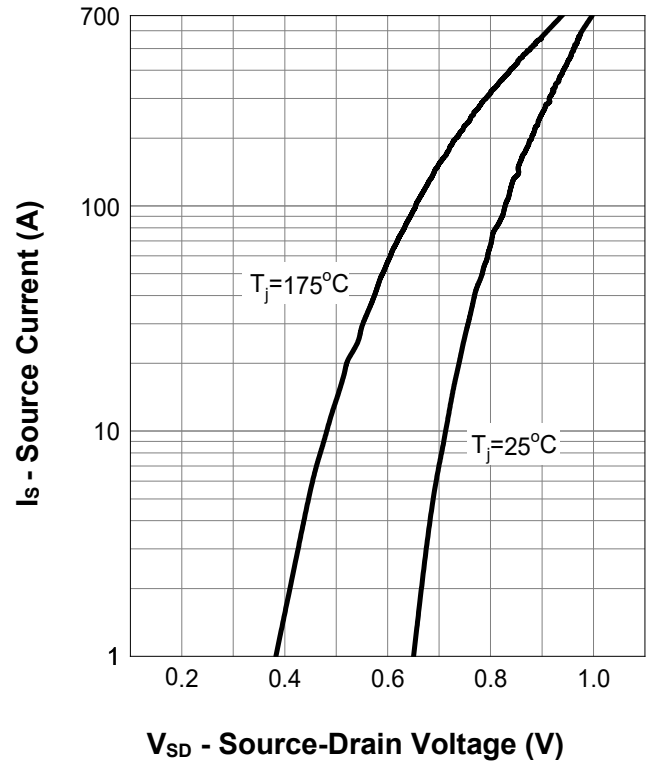


7. Typical Characteristics (cont.)

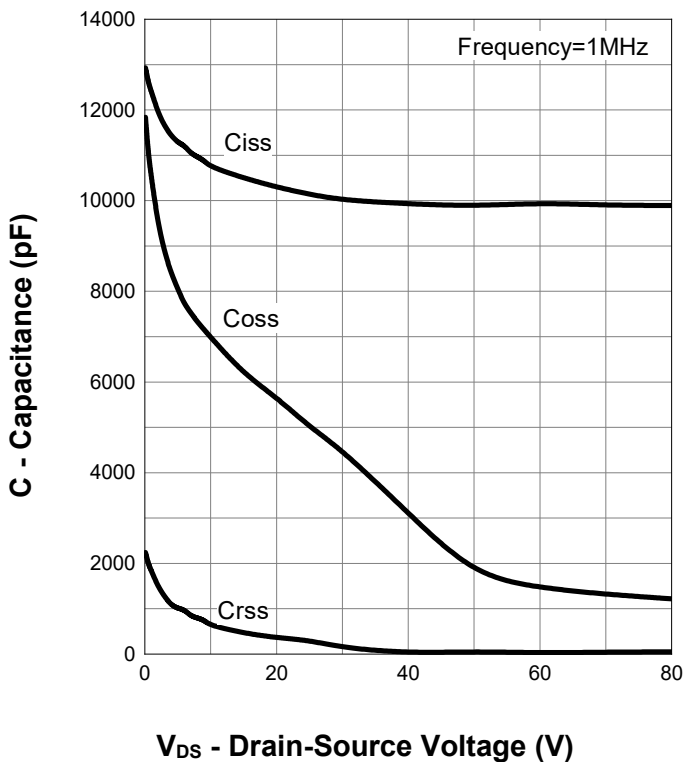
Normalized On Resistance



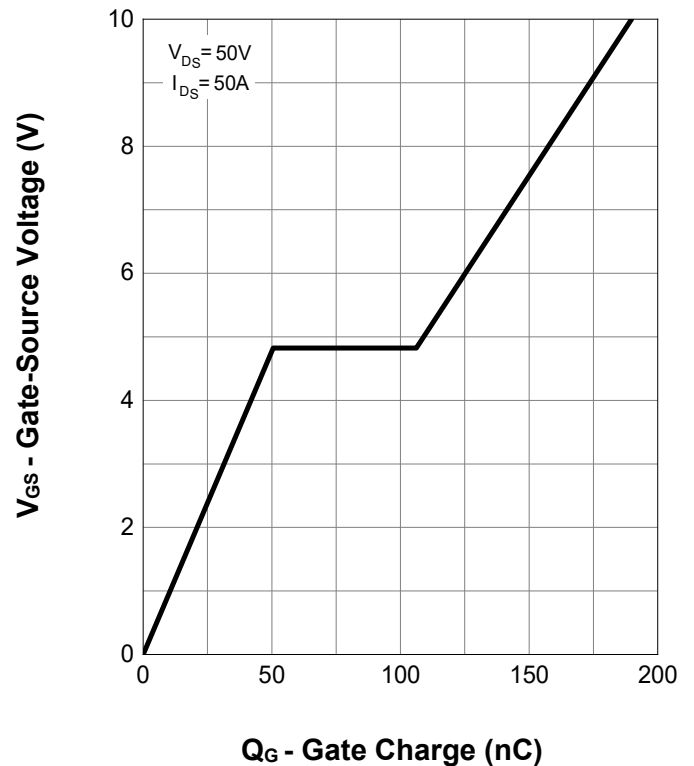
Diode Forward Current



Capacitance

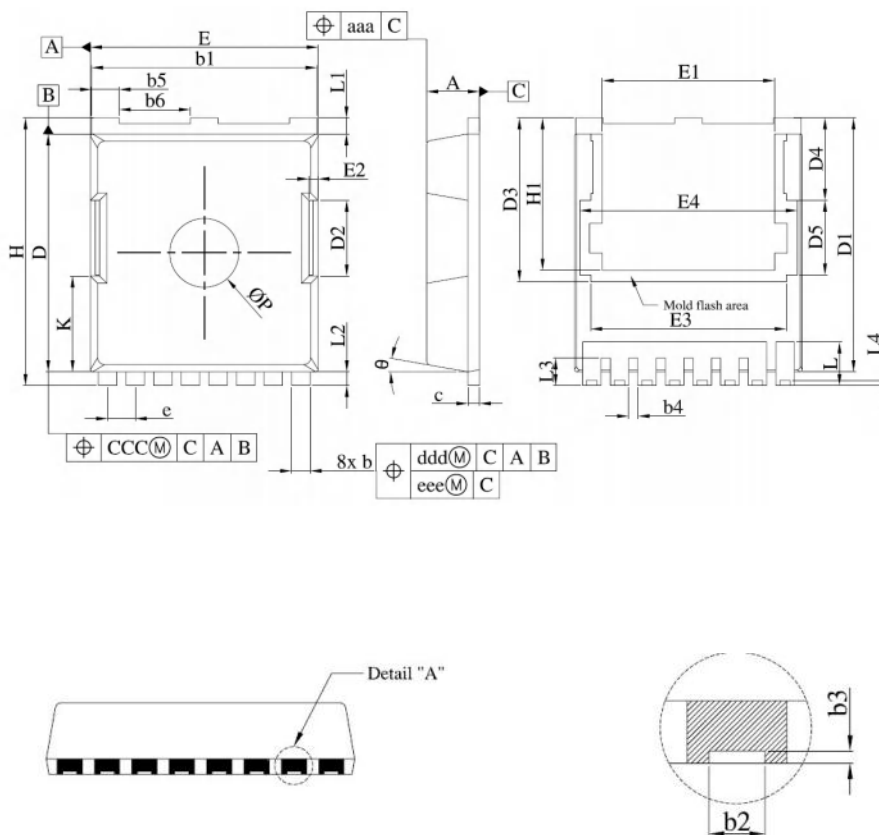


Gate Charge



8. Package Dimensions

TOLL-8L Package



Symbol	Dimensions In Millimeters		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.36	0.45	0.55
b3	0.05	0.10	/
b4	0.30	0.40	0.50
b5	1.10	1.20	1.30
b6	3.00	3.10	3.20
c	0.40	0.50	0.60
D	10.28	10.38	10.55
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3	7.15		
D4	3.59		
D5	3.26		
e	1.10	1.20	1.30
E	9.80	9.90	10.00
E1	7.40	7.50	7.60
E2	0.30	0.40	0.50
E3	8.50		
E4	9.46		
H	11.50	11.68	11.85
H1	6.55	6.65	6.75
K	4.08	4.18	4.28
L	1.60	1.90	2.10
L1	0.50	0.70	0.90
L2	0.50	0.60	0.70
L3	1.00	1.20	1.30
L4	0.13	0.23	0.33
p	2.85	3.00	3.15
θ	10°REF		
aaa	0.20		
ccc	0.20		
ddd	0.25		
eee	0.20		